

Modulation of electronic and magnetic properties of defective and TM-doped Al₂SSe Janus monolayer (TM = Mn and Fe) through hole and electron doping

Nguyen Thi Han,¹ Chu Viet Ha,² Nguyen Thanh Son,³ J. Guerrero-Sanchez,⁴ and D. M. Hoat^{5,6*}

¹Department of Basic Science, Hung Yen University of Technology and Education, Hung Yen, Vietnam

²Faculty of Physics, TNU-University of Education, Thai Nguyen, 250000, Vietnam

³Center of Scientific Research and Application, Lac Hong University, No.10 Huynh Van Nghe Str, Tran Bien Ward, Dong Nai Province, Vietnam

⁴Universidad Nacional Autónoma de México, Centro de Nanociencias y Nanotecnología, Apartado Postal 14, Ensenada, Baja California, Código Postal 22800, Mexico

⁵Institute of Theoretical and Applied Research, Duy Tan University, Ha Noi 100000, Viet Nam

⁶School of Engineering and Technology, Duy Tan University, Da Nang 550000, Viet Nam

*Corresponding author: dominhhoat@duytan.edu.vn

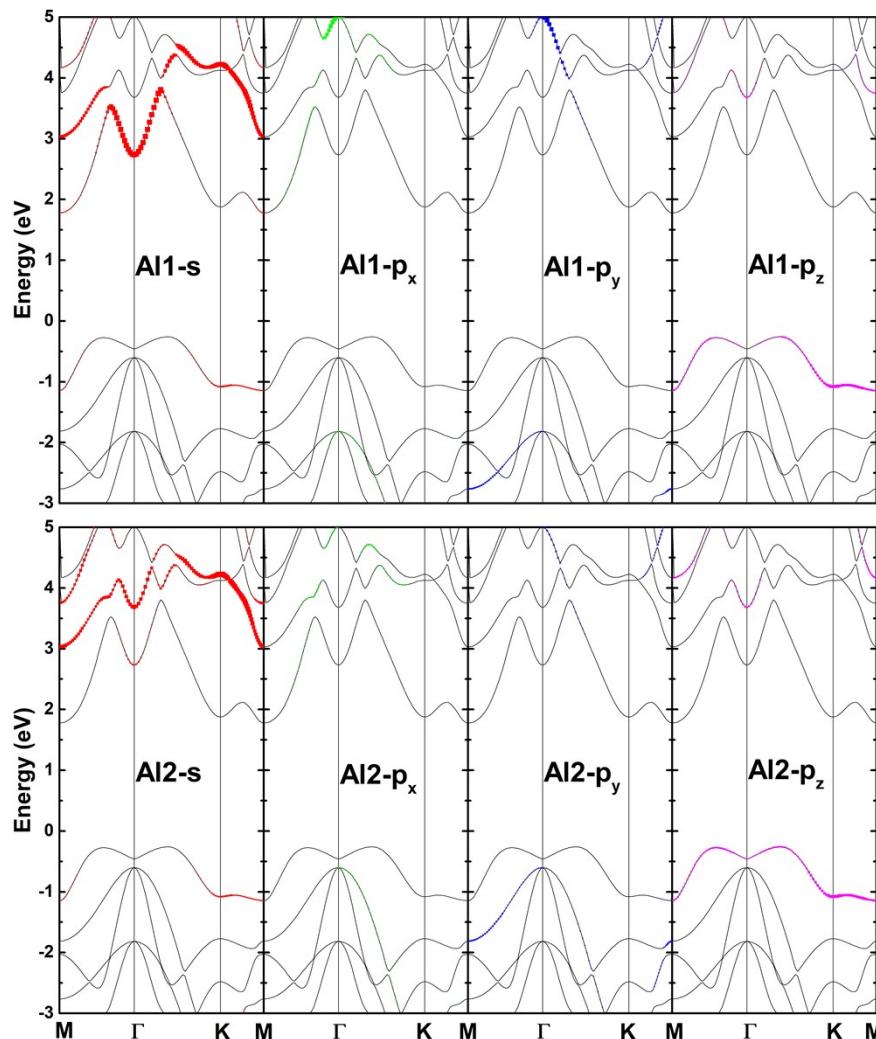


Figure S1: Orbital-decomposed band structure of Al_2SSe Janus monolayer (The Fermi level is set to 0 eV).

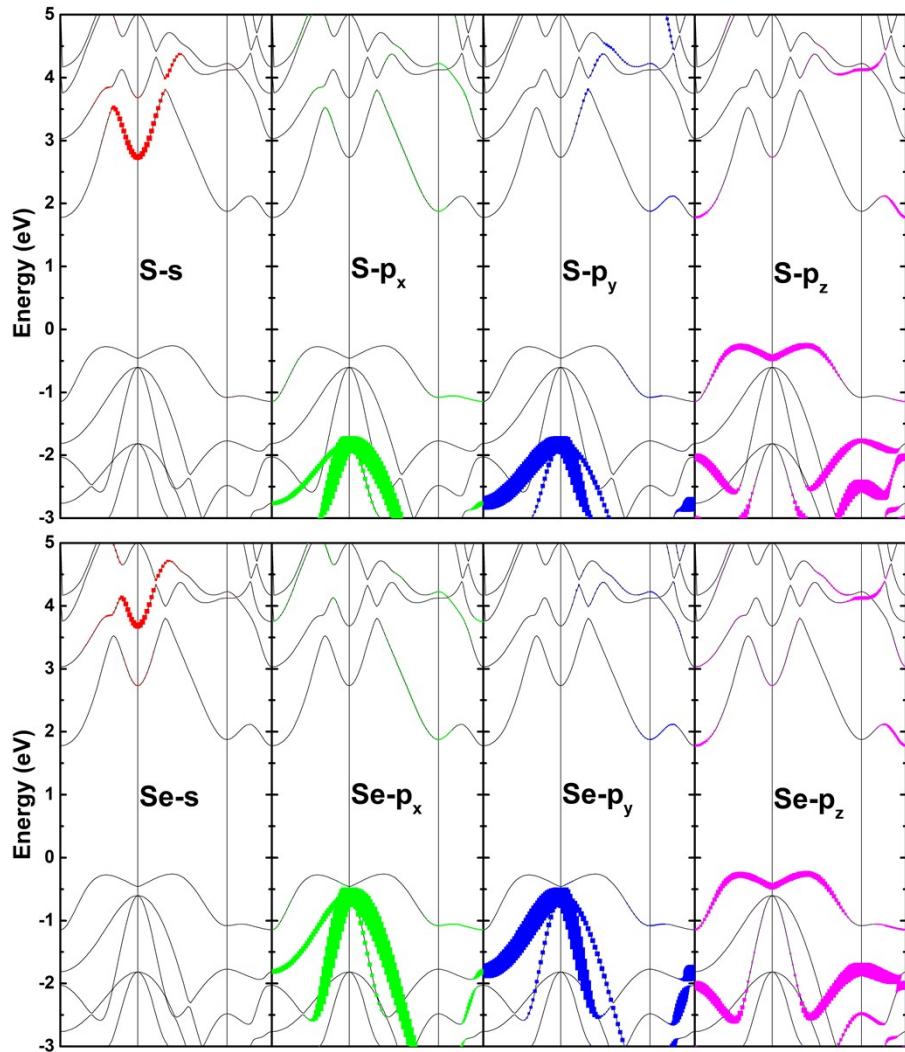


Figure S1 (cont): Orbital-decomposed band structure of Al_2SSe Janus monolayer (The Fermi level is set to 0 eV).